



Hidden pits of SiC MOSFET benchmarking and evaluation

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**Bodo's
Wide Bandgap
Event 2024**

Making WBG Designs Happen

SiC

ST silicon carbide business

Business Development

~85 customers, ~130 programs awarded
\$1.14B revenues in 2023 (+60% vs. 2022)
\$5B+ revenue opportunity by 2030
>40% market share in SiC MOSFETs and power modules

Source: Omdia

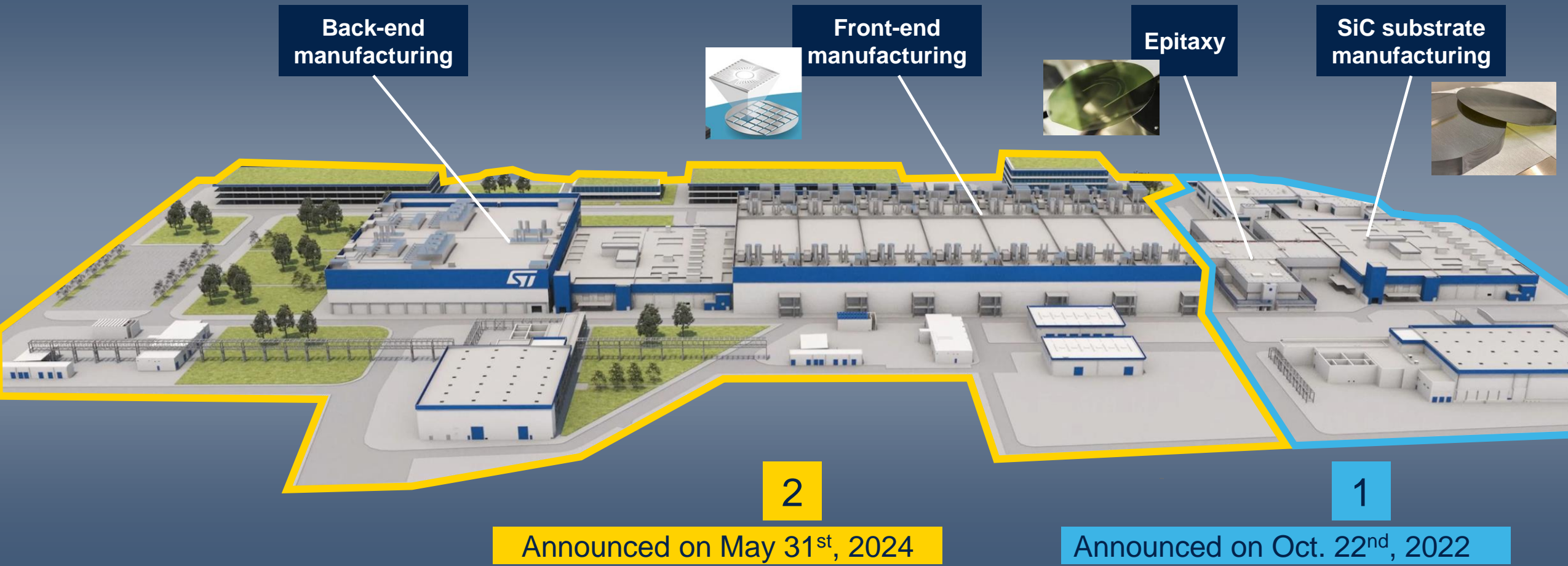
Portfolio & technology

Portfolio of SiC MOSFETs & diodes

- 650V to 1700V SiC MOSFET product range
- 3rd generation MOSFETs in high-volume production
- Flexible approach covering discrete packages, modules, dice

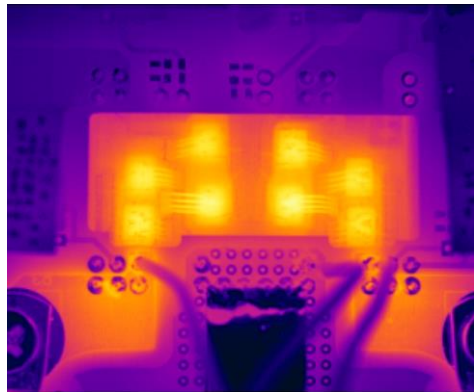
ST silicon carbide campus in Catania

Vertically integrated silicon carbide facility



SiC MOSFET Benchmarking

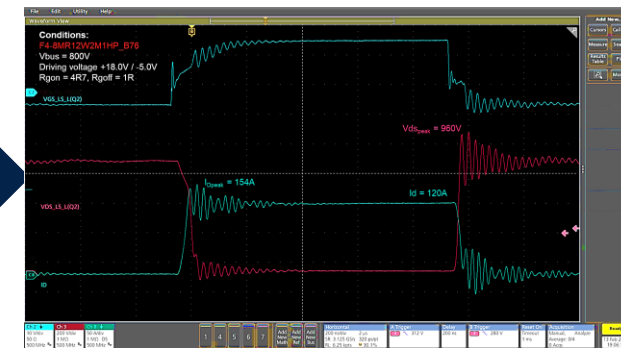
Efficiency Benchmarking of the devices



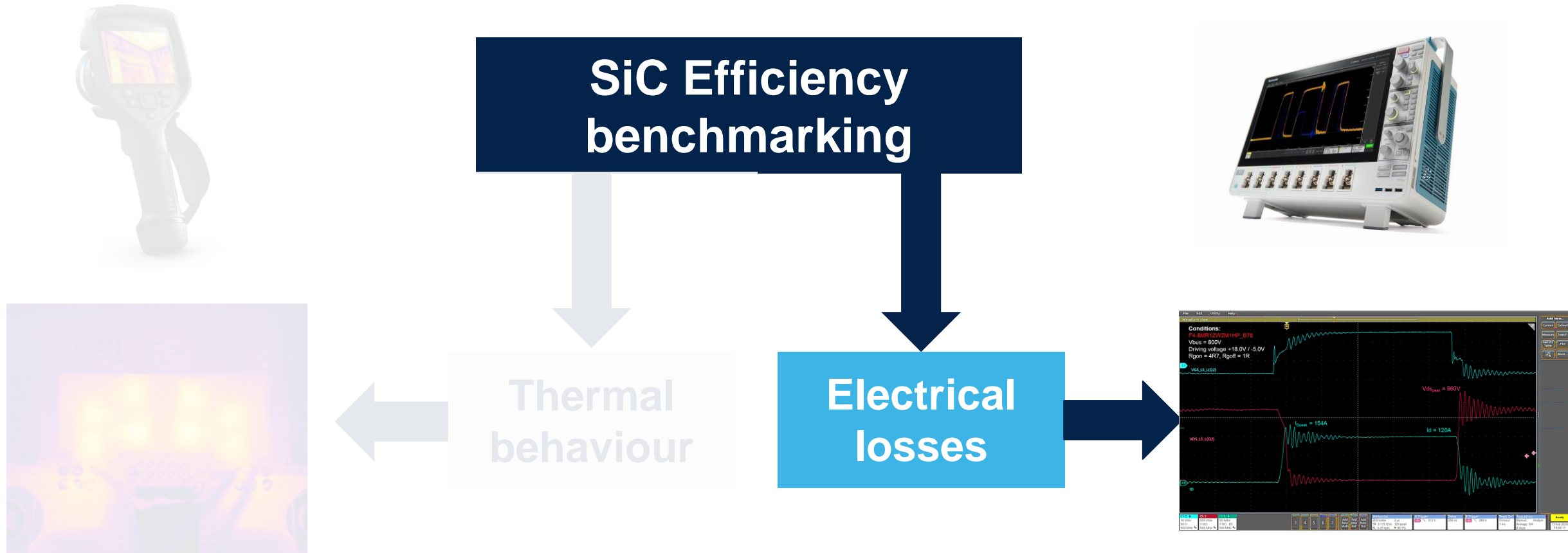
SiC Efficiency benchmarking

Thermal behaviour

Electrical losses

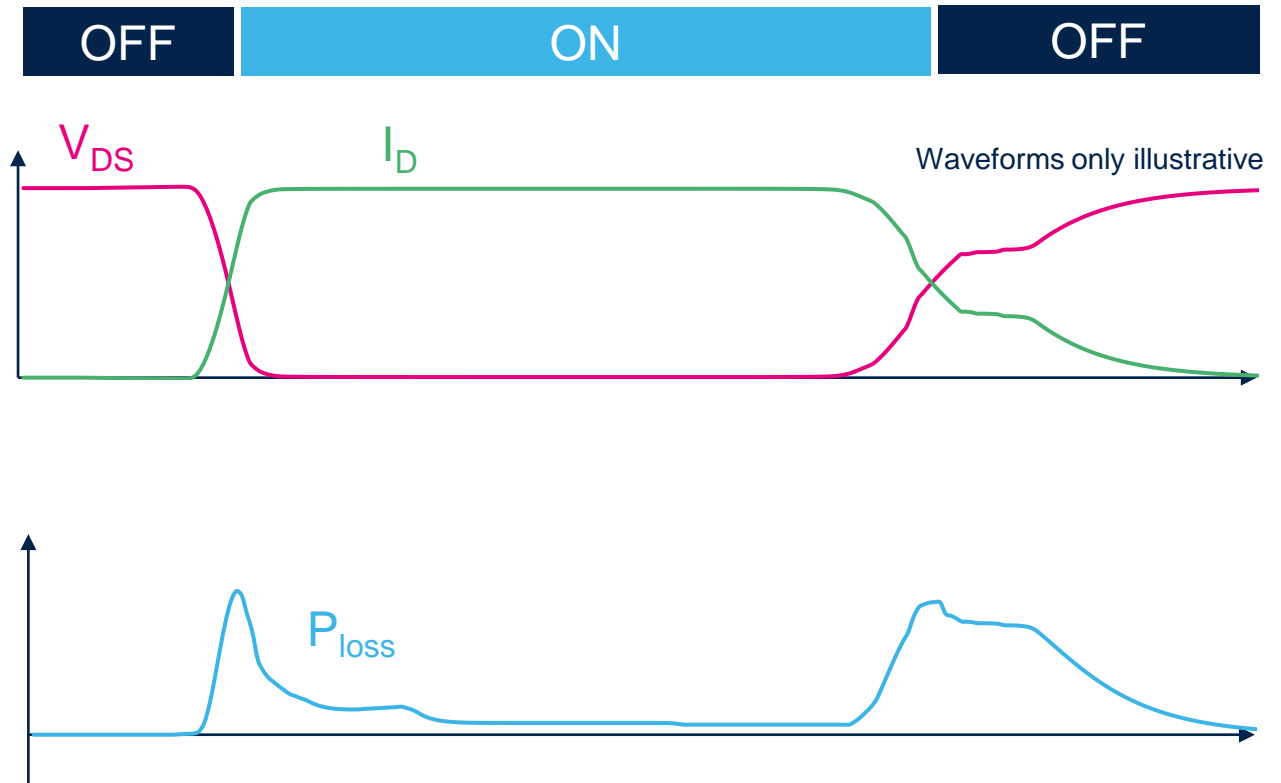
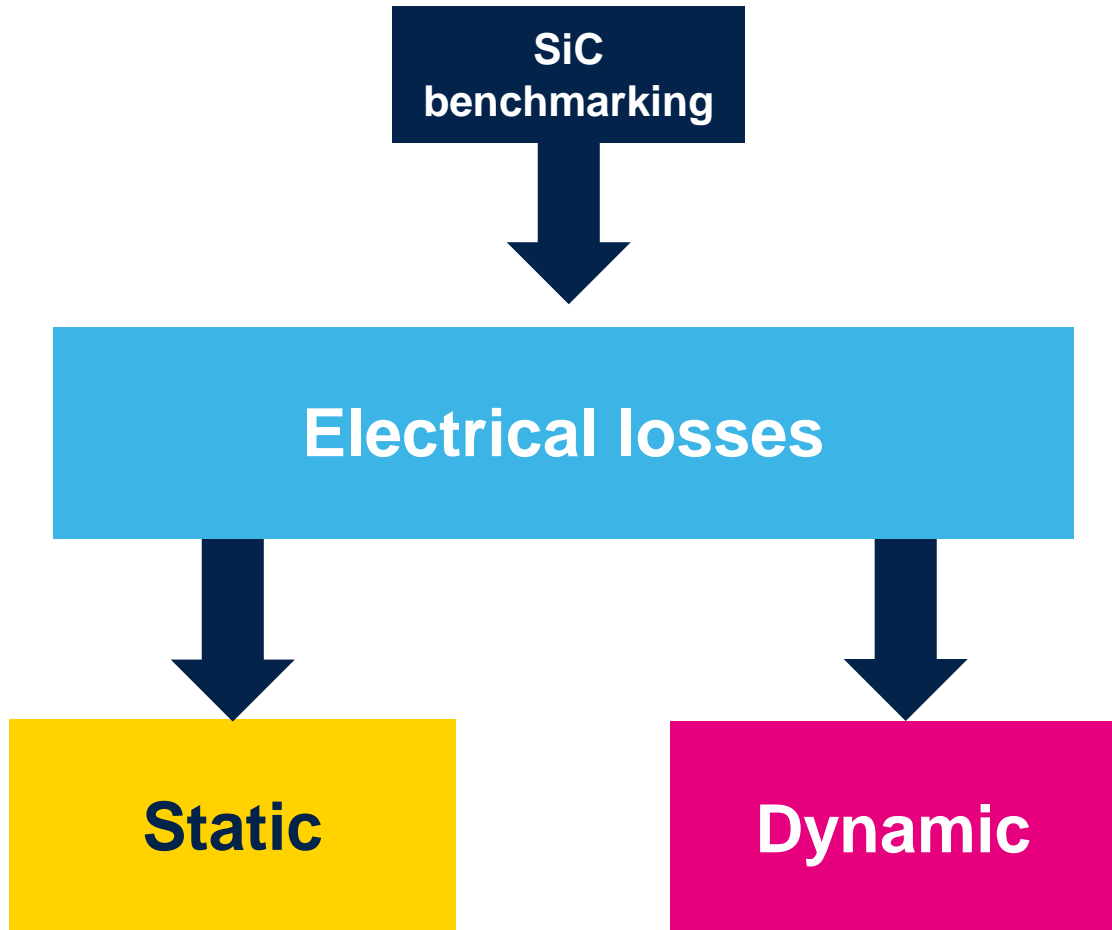


Efficiency Benchmarking of the devices

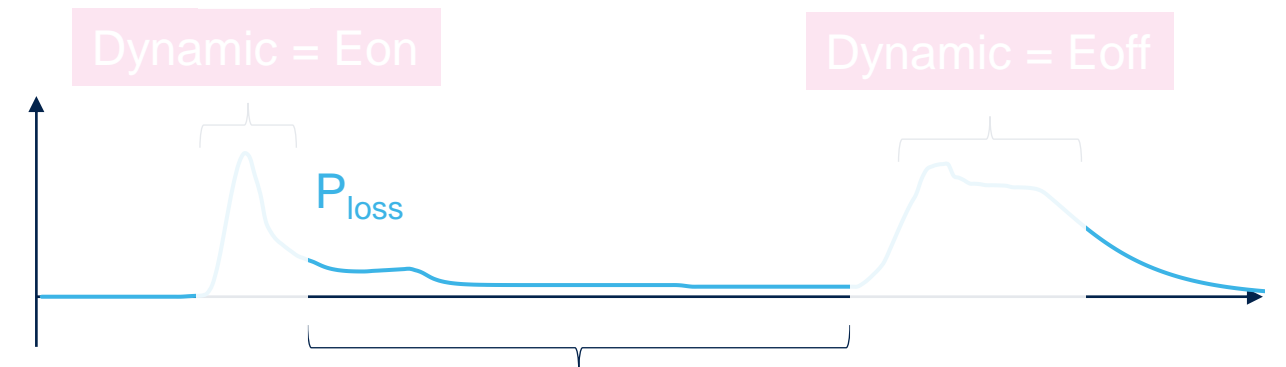
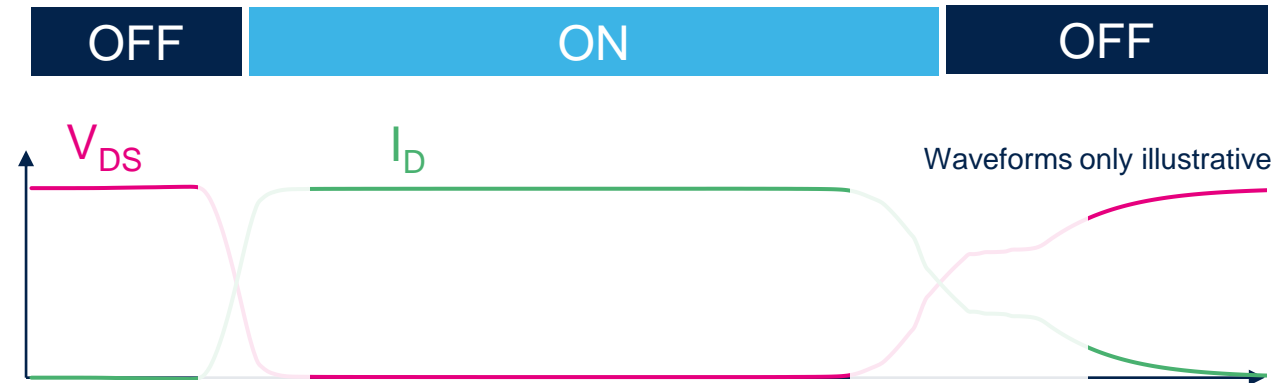
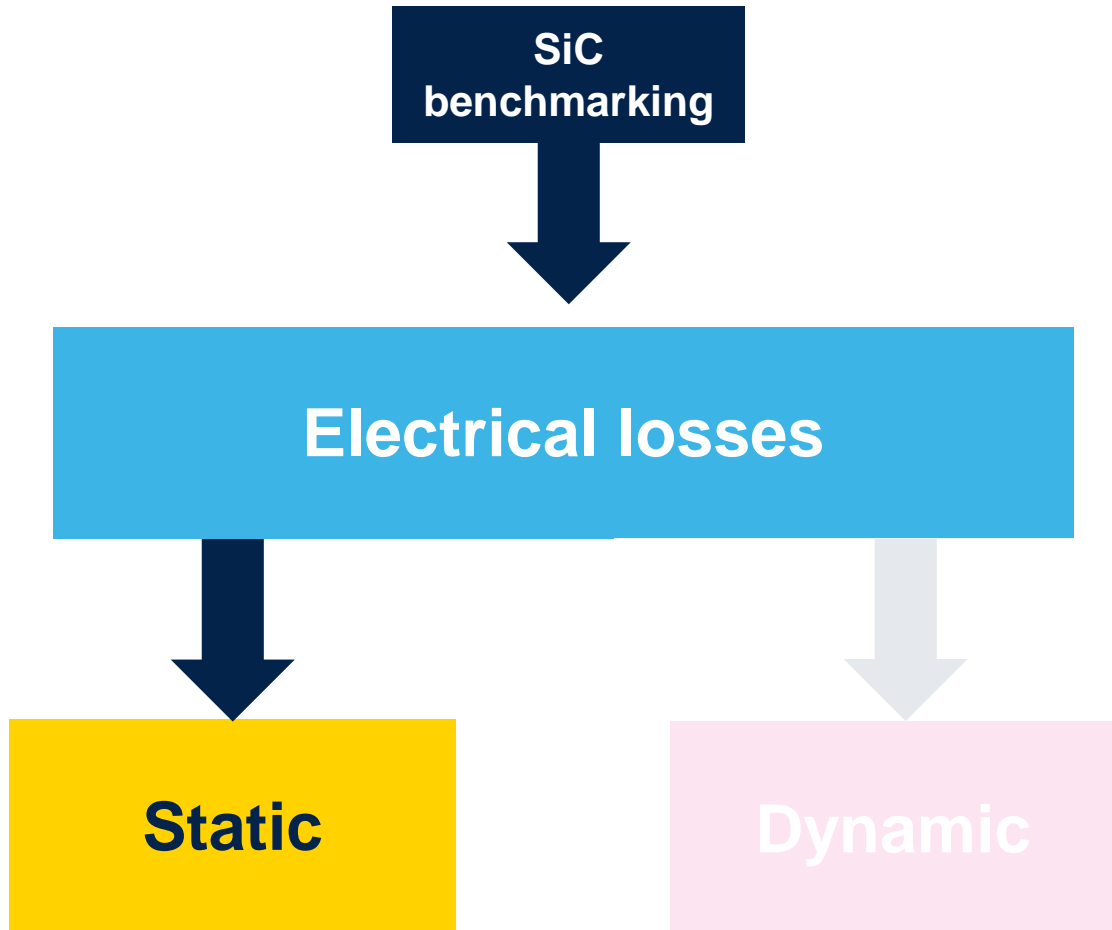


Benchmarking of the devices

electrical behavior

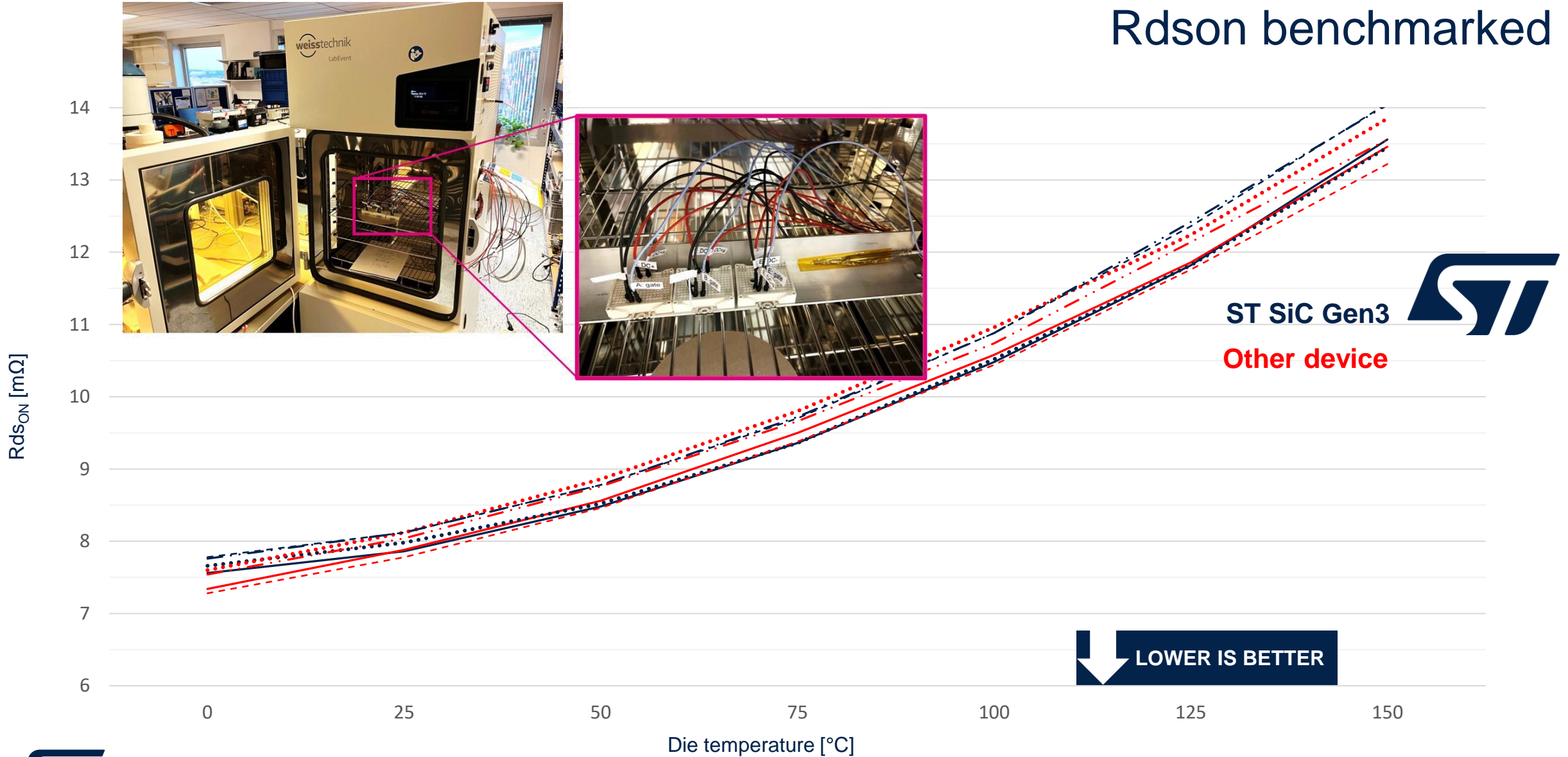


Benchmarking of the devices electrical behavior



$$P_{stat} = R_{DSon} * (I_{d_{RMS}})^2$$

Static losses Rdson benchmarked



ST SiC Gen3

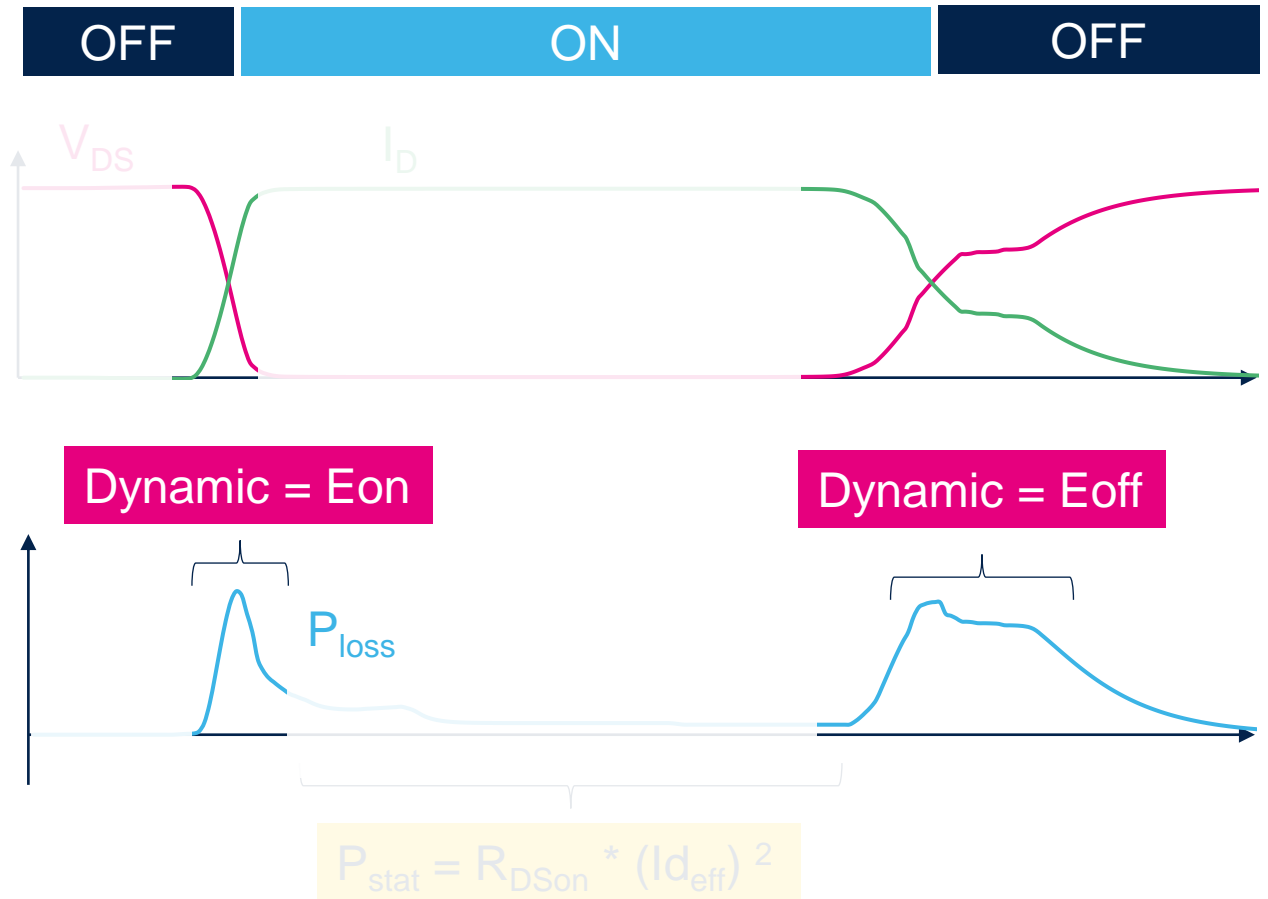
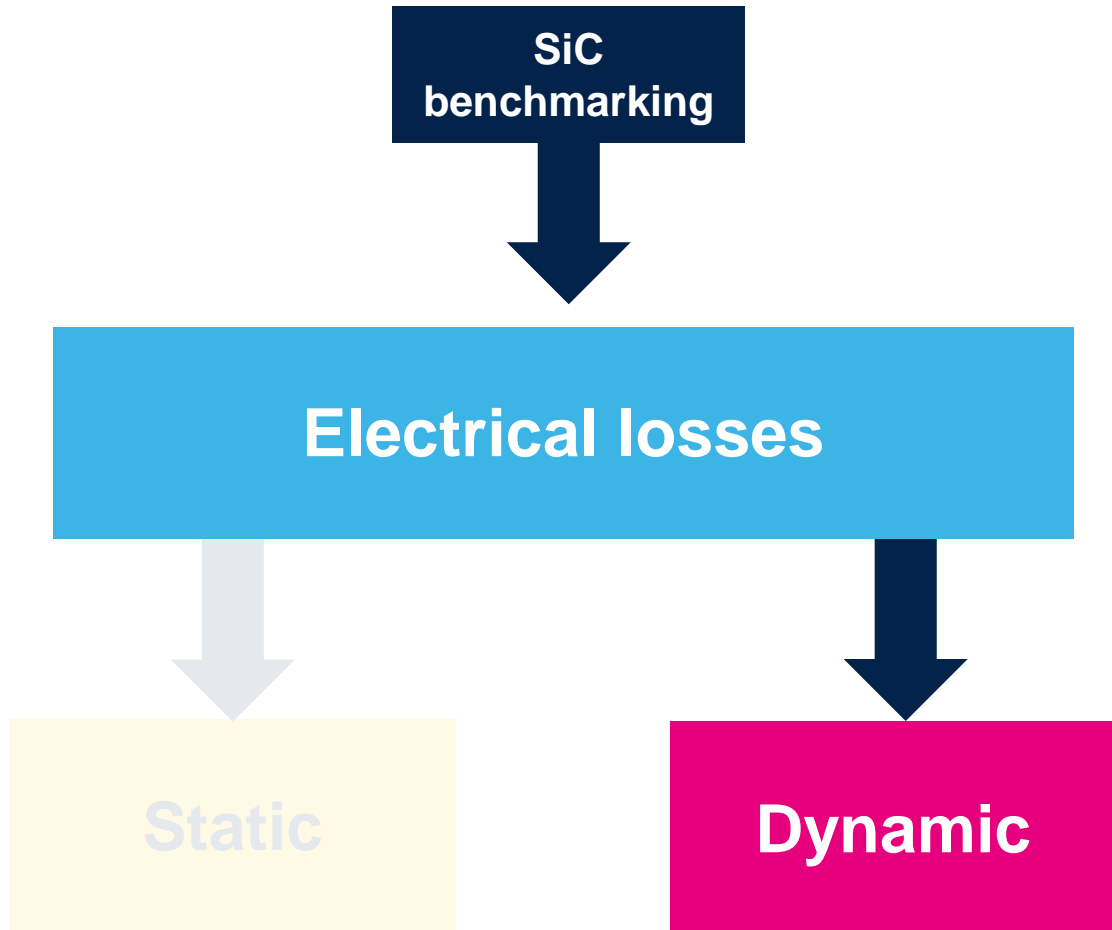


Other device

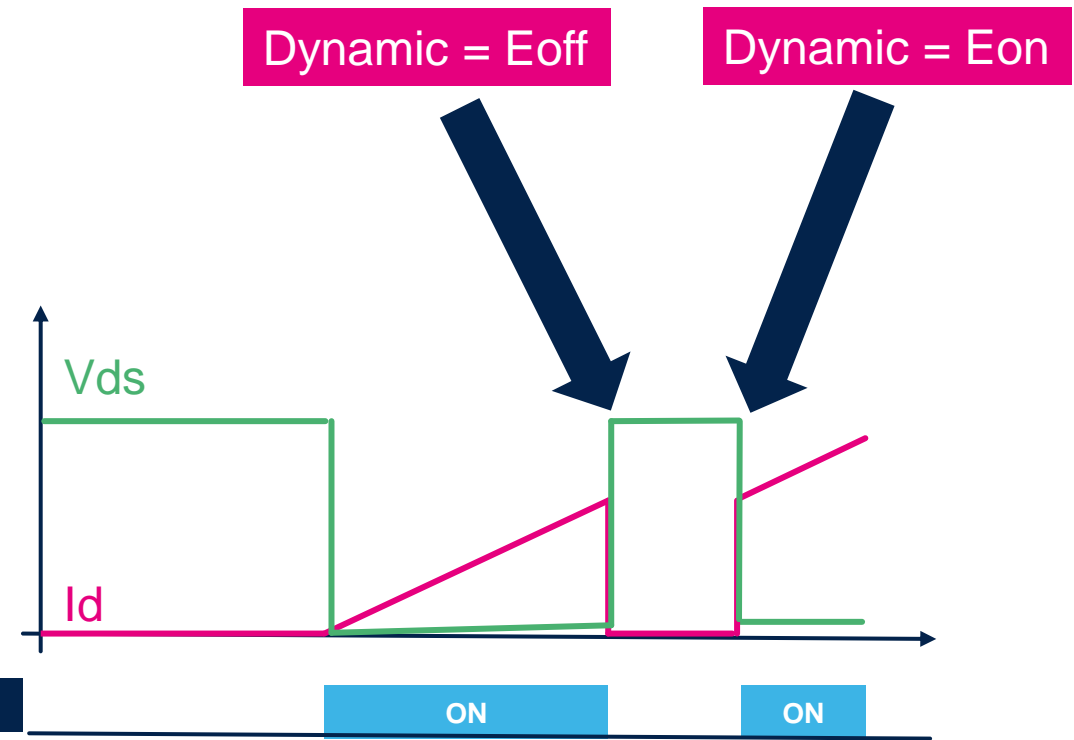
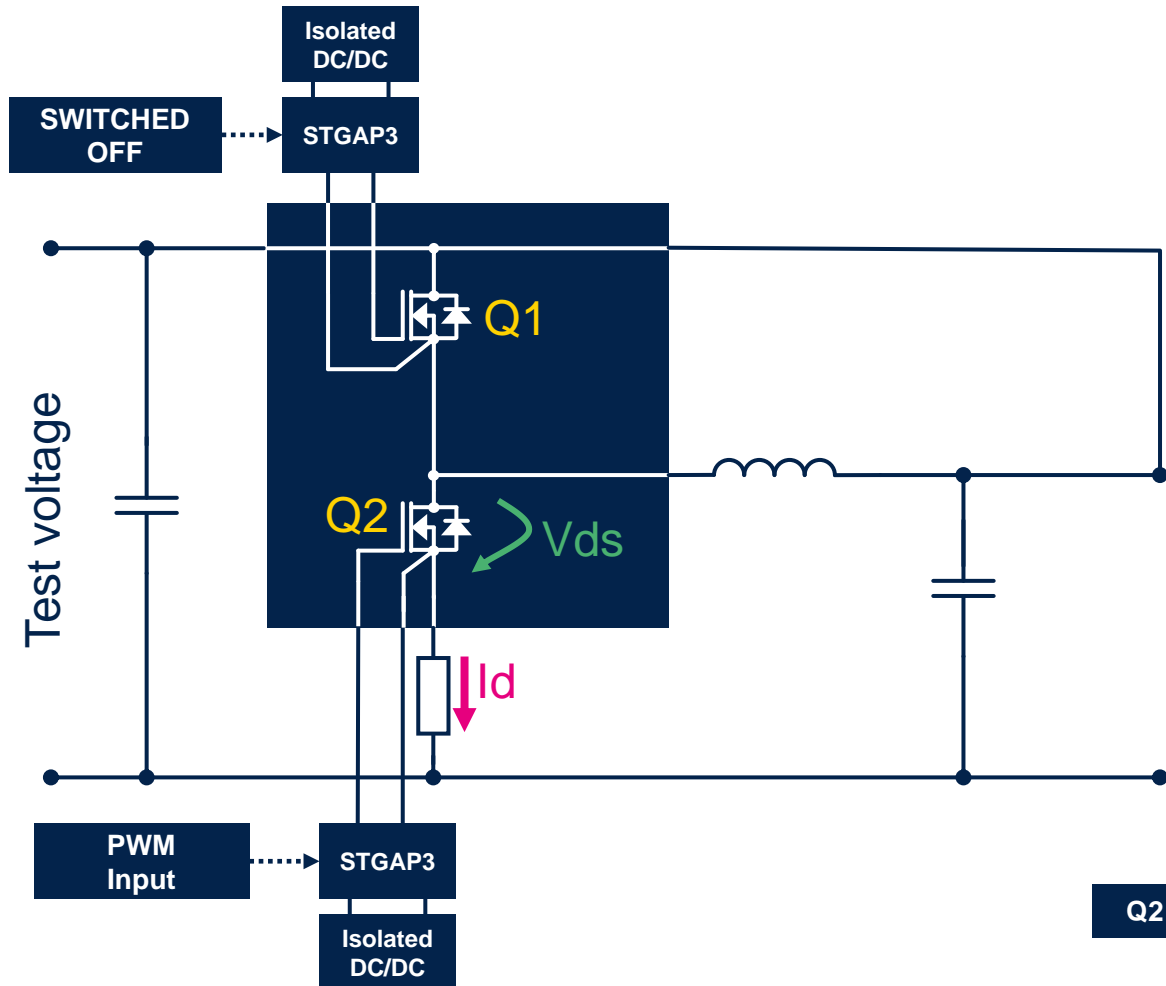
↓ LOWER IS BETTER

Benchmarking of the devices

electrical behavior



Double pulse test setup



Voltage measurement:

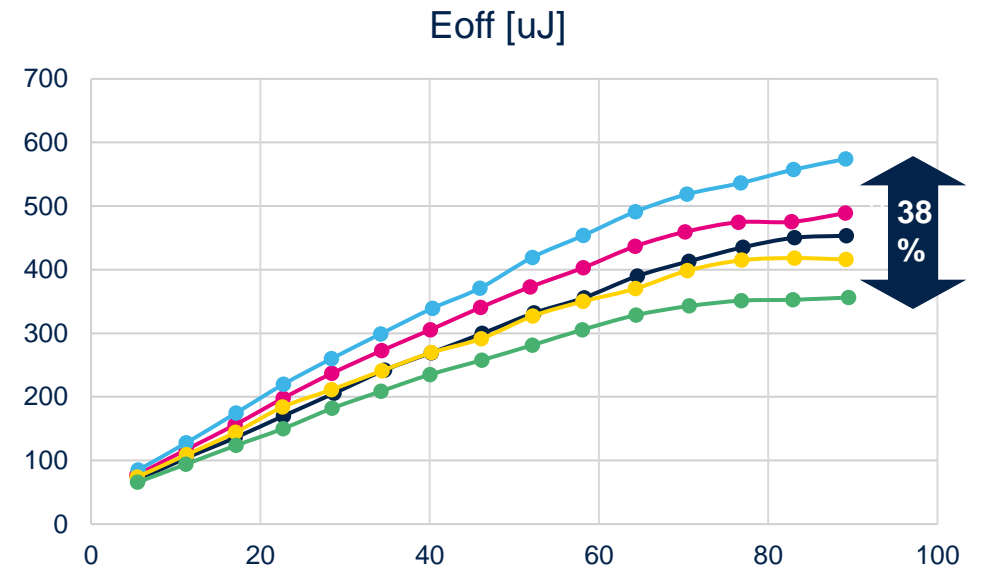
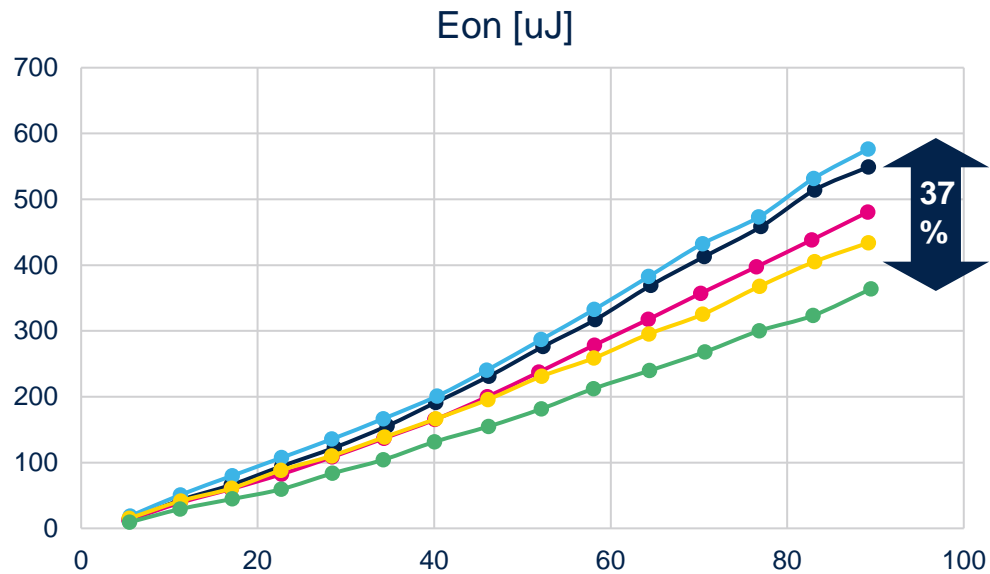
- HV passive probe 100:1 - 250MHz
- HV passive probe 100:1 - 400MHz
- Differential Probe IsoVu 500V 1GHz
- Differential Probe BumbleBee 1000V 400MHz
-



Current measurement:

- Coaxial shunt 50mΩ
- Rogowski coil 20MHz
-

Double pulse testing - Effect of different voltage probes

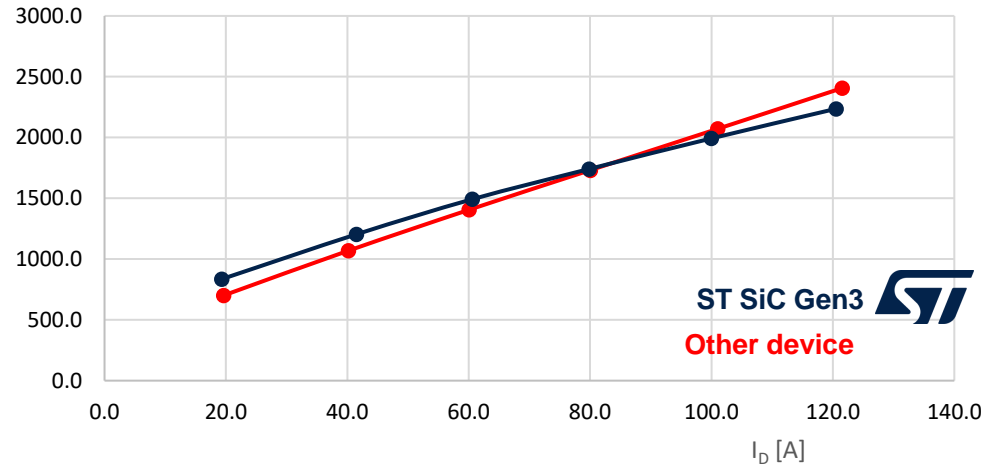


- HV passive probe 100:1 - 250MHz
- HV passive probe 100:1 - 400MHz
- IsoVu 500V 1GHz
- IsoVu 500V 1GHz with offset comp.
- IsoVu 500V 1GHz after new self calib.

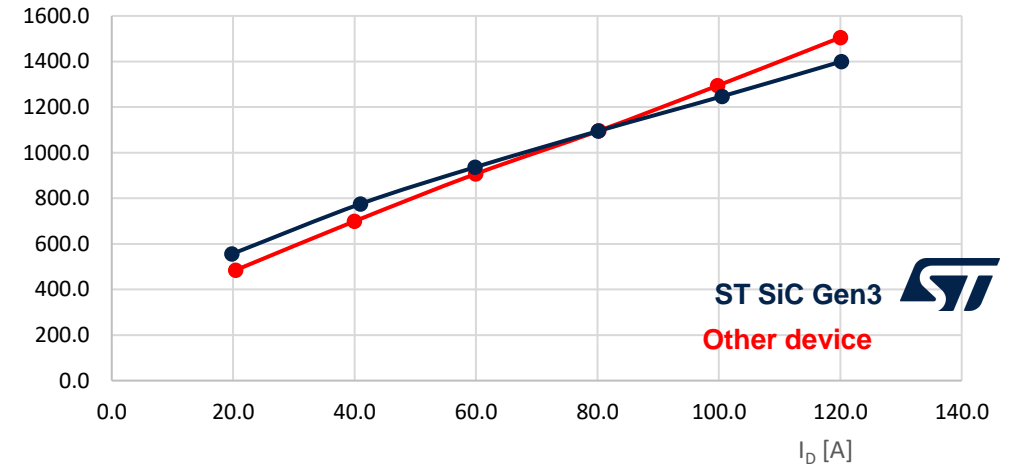
Dynamic Losses

Eon – Eoff Comparison/benchmark

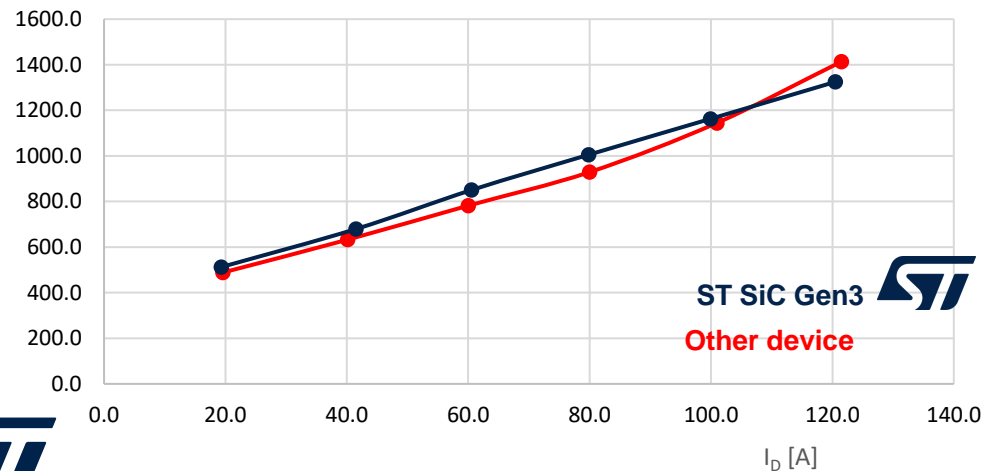
Eon [uJ] - 800V



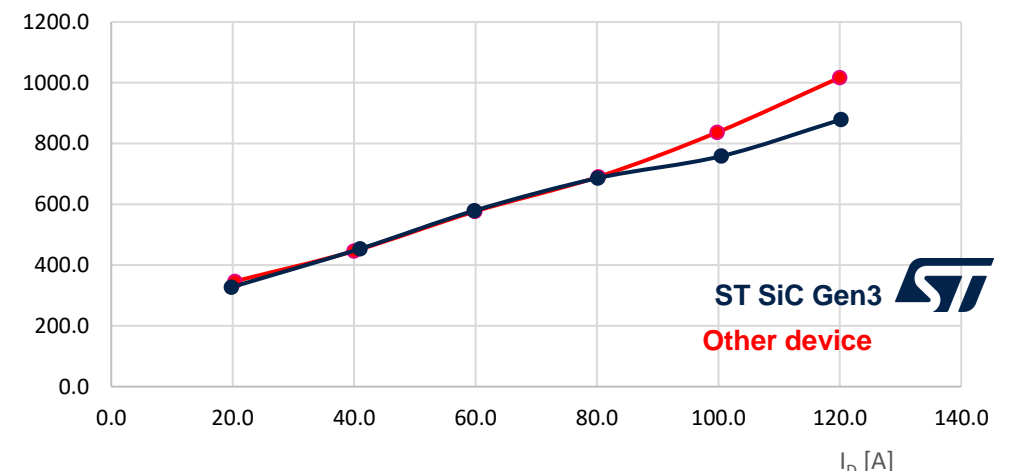
Eon [uJ] - 600V



Eoff [uJ] - 800V



Eoff [uJ] - 600V



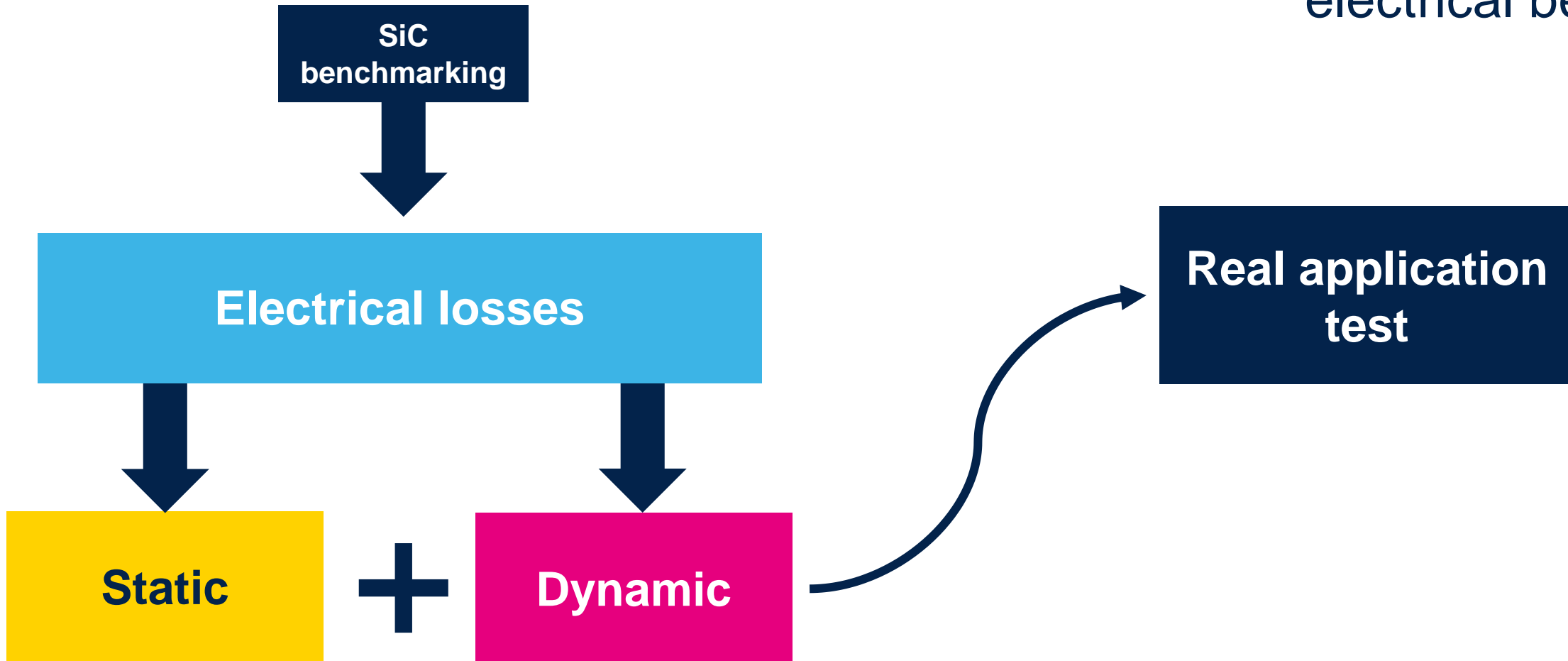


life.augmented

Full application tests

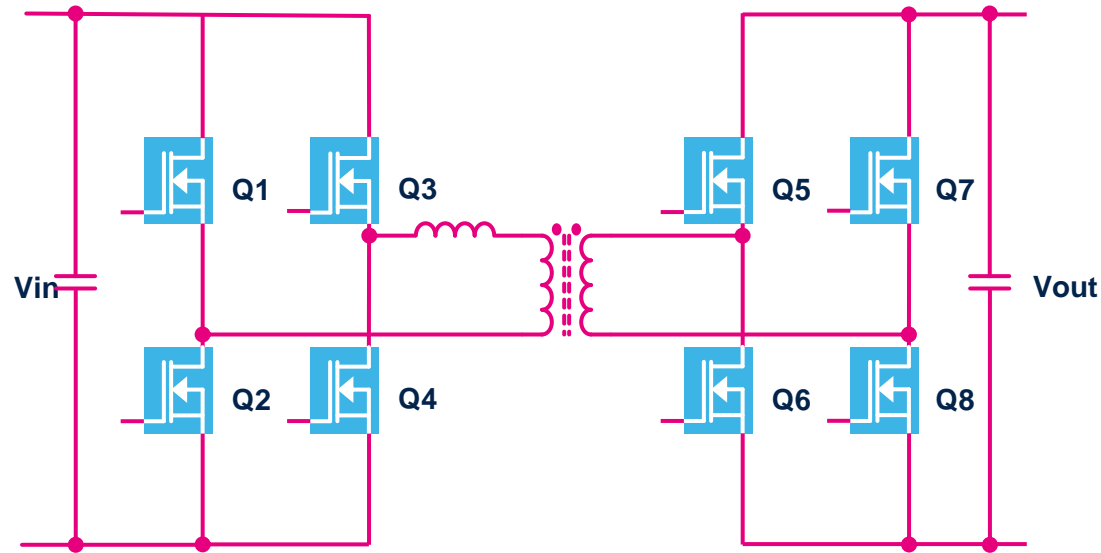


Benchmarking of the devices electrical behavior

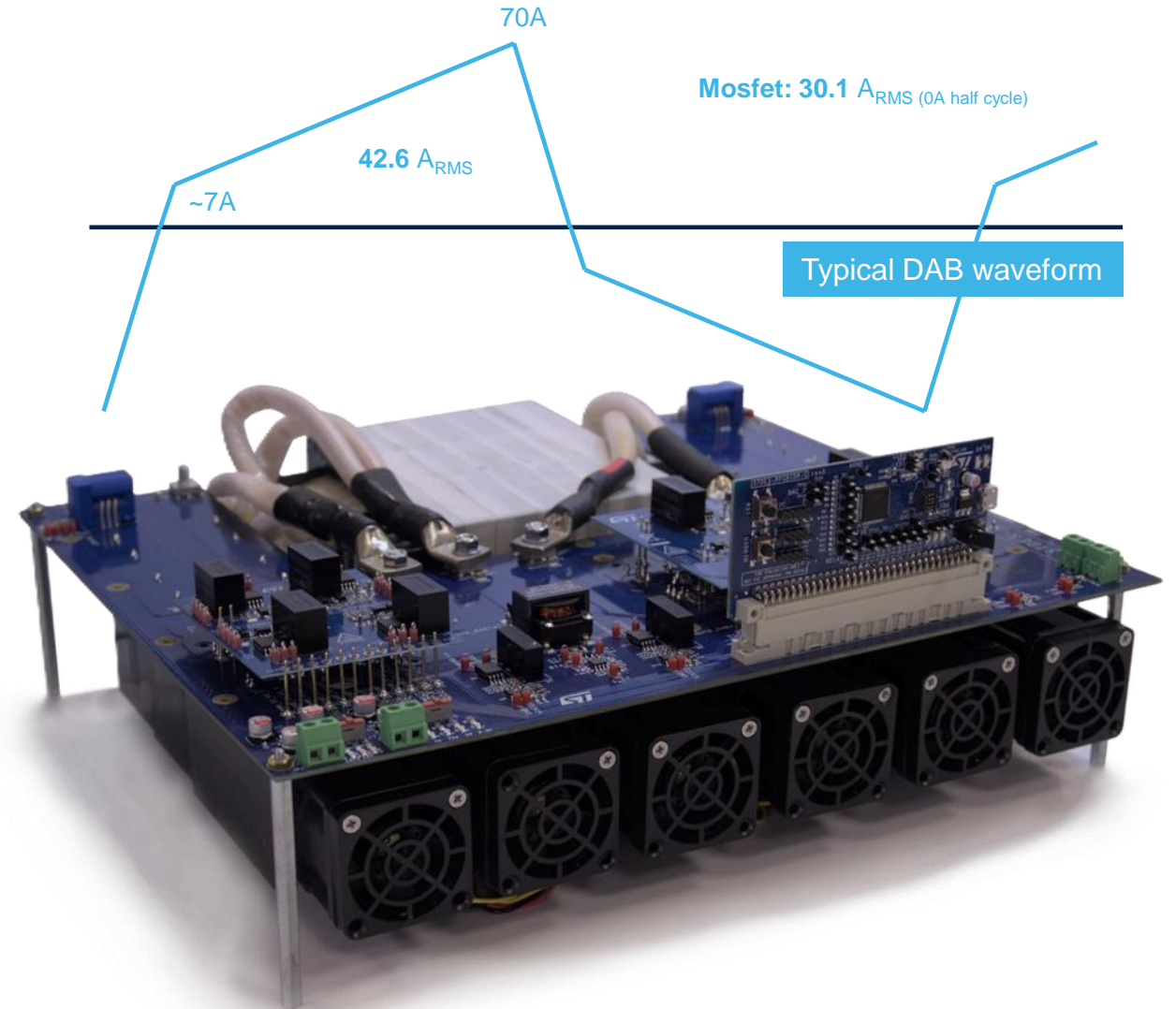


Dual Active Bridge Structure & waveform example

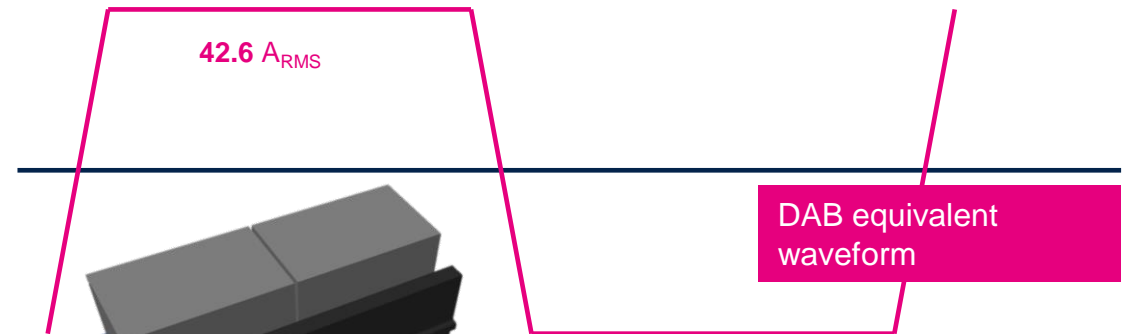
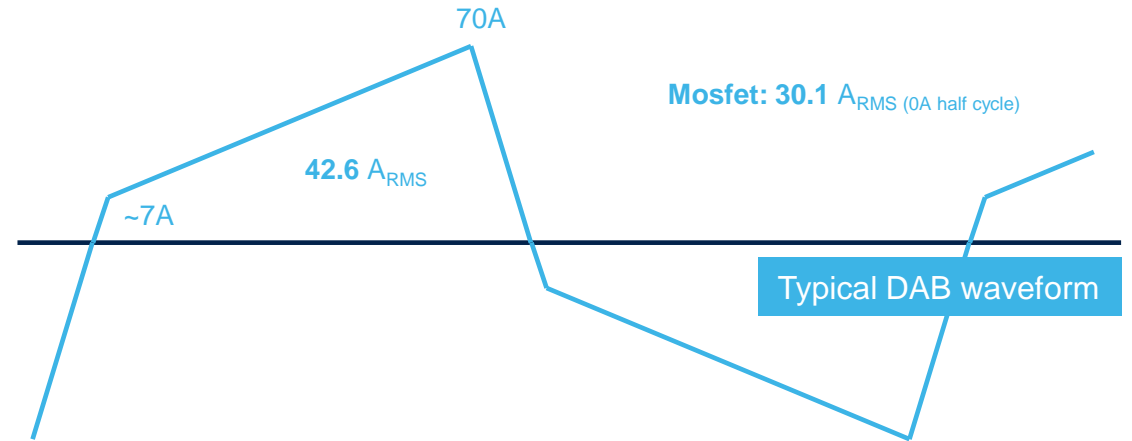
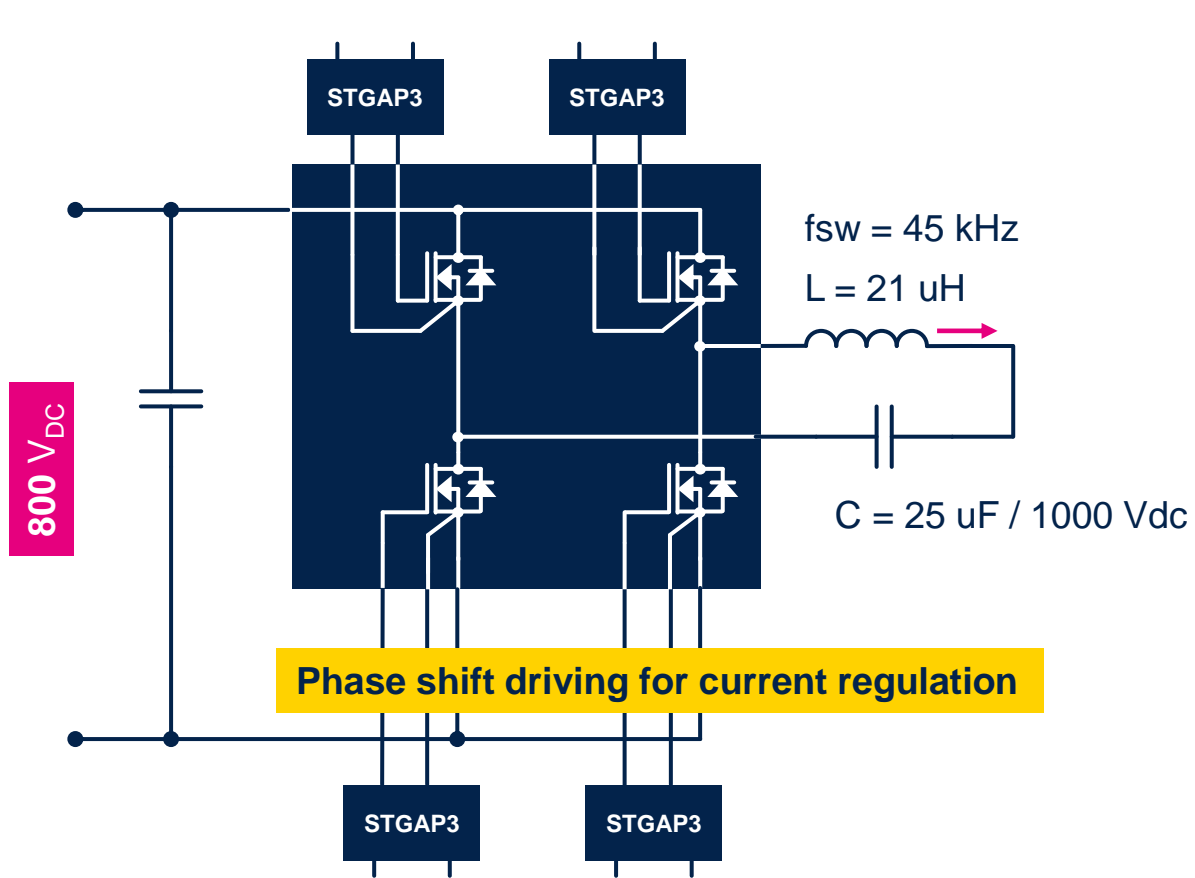
- DAB real block scheme



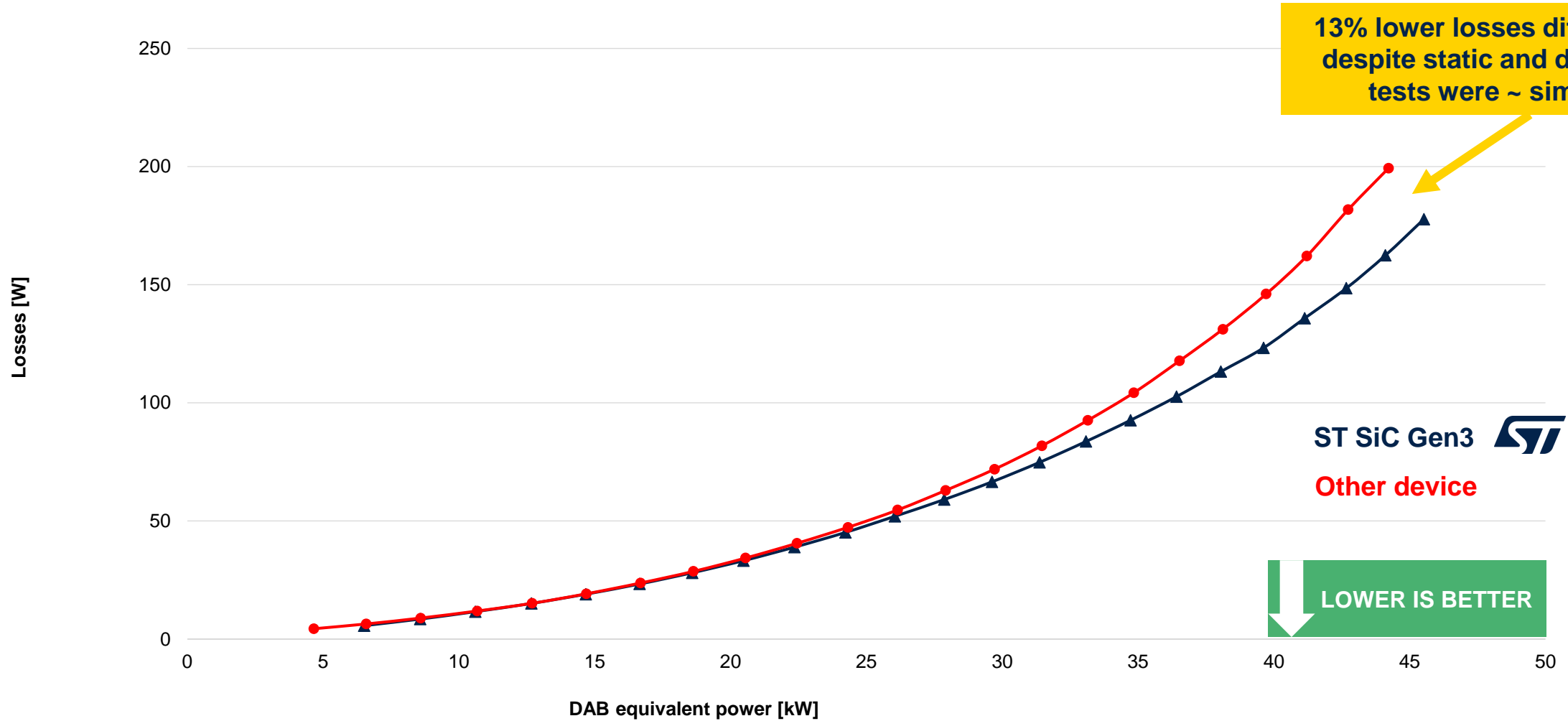
The best, but too complex



Simplified converter with same device's stress



DAB testing method Efficiency Result



Our technology starts with You



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Bonus slide

Hidden pits

Hidden pits

Application Measurement example

- Positive oscillations seen by probe A
- **Application was running perfectly**
- Negative oscillations seen by probe A with switched connectors
- Oscillations not seen by probe type B

